

Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	40	V
Collector-Emitter Voltage	V _{CEO}	40	V
Emitter-Base Voltage	V_{EBO}	5	V
Peak Pulse Collector Current	I _{CM}	3	A
Continuous Collector Current	I _C	2	A
Peak Base Current	I _{BM}	0.3	A

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P _D	730	mW
Power Dissipation (Note 6)	P _D	600	mW
Thermal Resistance, Junction to Ambient Air (Note 5)	R _{θJA}	171	°C/W
Thermal Resistance, Junction to Ambient Air (Note 6)	R _{θJA}	209	°C/W
Thermal Resistance, Junction to Lead (Note 7)	R _{θJL}	75	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes:

- 5. For a device mounted with the collector lead on 15mm x 15mm 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.

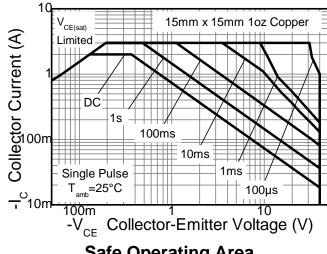
 6. Same as note (5), except the device is mounted on minimum recommended pad layout.

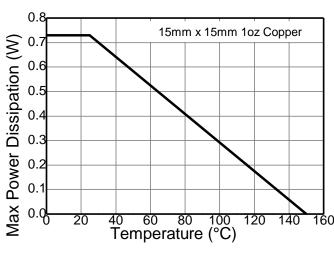
 7. Thermal resistance from junction to solder-point (at the end of the collector lead).

 8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



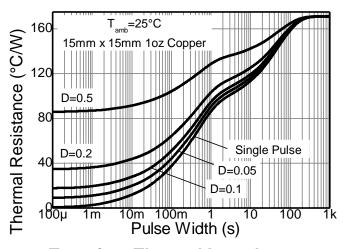
Thermal Characteristics and Derating Information

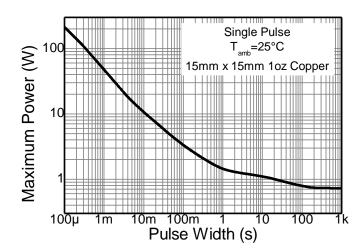












Transient Thermal Impedance

Pulse Power Dissipation



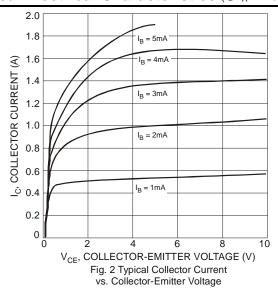
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

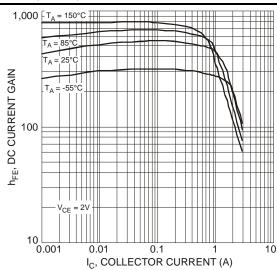
Characteristic	Symbol	Min	Тур	Max	Unit	Test Conditions
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	BV_{CBO}	40	_	_	V	I _C = 100μA
Collector-Emitter Breakdown Voltage (Note 8)	BV _{CEO}	40	_	_	V	I _C = 10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	5			V	I _E = 100μA
Collector-Base Cutoff Current				100	nA	$V_{CB} = 30V, I_{E} = 0$
Collector-base Cuton Current	Ісво	_	_	50	μΑ	$V_{CB} = 30V$, $I_E = 0$, $T_A = +150$ °C
Emitter-Base Cutoff Current	I _{EBO}	_	_	100	nA	$V_{EB} = 4V, I_{C} = 0$
ON CHARACTERISTICS (Note 8)						
		350	_	_		$V_{CE} = 2V, I_{C} = 0.1A$
DC Current Gain	b	300	_			$V_{CE} = 2V, I_{C} = 0.5A$
DC Current Gain	hFE	300	_			$V_{CE} = 2V$, $I_C = 1A$
		150				$V_{CE} = 2V$, $I_C = 2A$
				70		$I_C = 100 \text{mA}, I_B = 1 \text{mA}$
			30	100	mV	$I_C = 500 \text{mA}, I_B = 50 \text{mA}$
Collector-Emitter Saturation Voltage	V _{CE(SAT)}			180		I _C = 750mA, I _B = 15mA
				180		$I_C = 1A$, $I_B = 50mA$
				320		$I_C = 2A$, $I_B = 200mA$
Equivalent On-Resistance	R _{CE(SAT)}		60	200	mΩ	$I_C = 500 \text{mA}, I_B = 50 \text{mA}$
Base-Emitter Saturation Voltage	V _{BE(SAT)}			1.1	V	$I_C = 2A$, $I_B = 200mA$
Base-Emitter Turn-On Voltage	V _{BE(ON)}	_		0.75	V	$V_{CE} = 2V, I_{C} = 100mA$
SMALL SIGNAL CHARACTERISTICS						
Transition Frequency	f _T	100	_	_	MHz	$V_{CE} = 10V, I_{C} = 100mA,$ f = 100MHz
Output Capacitance	C _{OB}			20	pF	V _{CB} = 10V, f = 1MHz
Turn-On Time	t _{ON}		43	-	ns	I _C =500mA, V _{CC} =10V,
Turn-Off Time	t _{OFF}	_	363	_	ns	$I_{B1} = -I_{B2} = 50 \text{mA}$

Note:

8. Measured under pulsed conditions. Pulse width $\leq 300 \mu s.$ Duty cycle $\leq 2\%.$

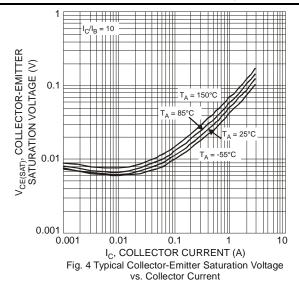
Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

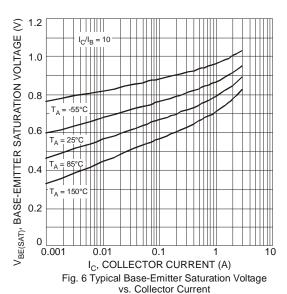


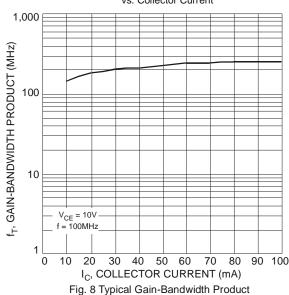




Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.) (Continued)







vs. Collector Current

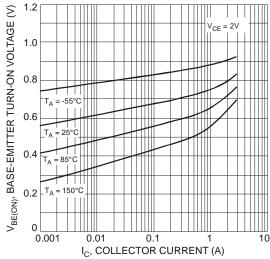


Fig. 5 Typical Base-Emitter Turn-On Voltage vs. Collector Current

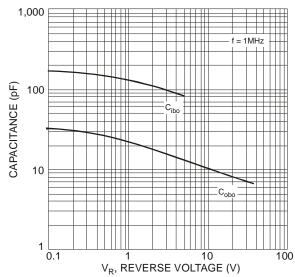


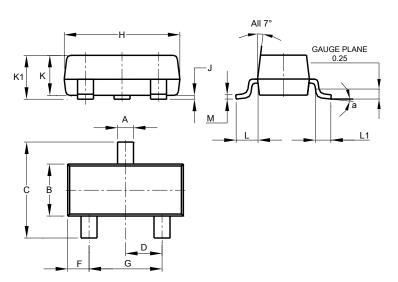
Fig. 7 Typical Capacitance Characteristics



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23

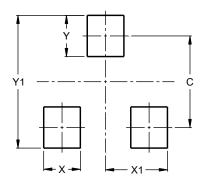


SOT23					
Dim	Min	Max	Тур		
Α	0.37	0.51	0.40		
В	1.20	1.40	1.30		
С	2.30	2.50	2.40		
D	0.89	1.03	0.915		
F	0.45	0.60	0.535		
G	1.78	2.05	1.83		
Η	2.80	3.00	2.90		
J	0.013	0.10	0.05		
K	0.890	1.00	0.975		
K1	0.903	1.10	1.025		
L	0.45	0.61	0.55		
L1	0.25	0.55	0.40		
M	0.085	0.150	0.110		
а	0°	8°			
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23



Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Y	0.9
Y1	2.9



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